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**EXHIBIT N**

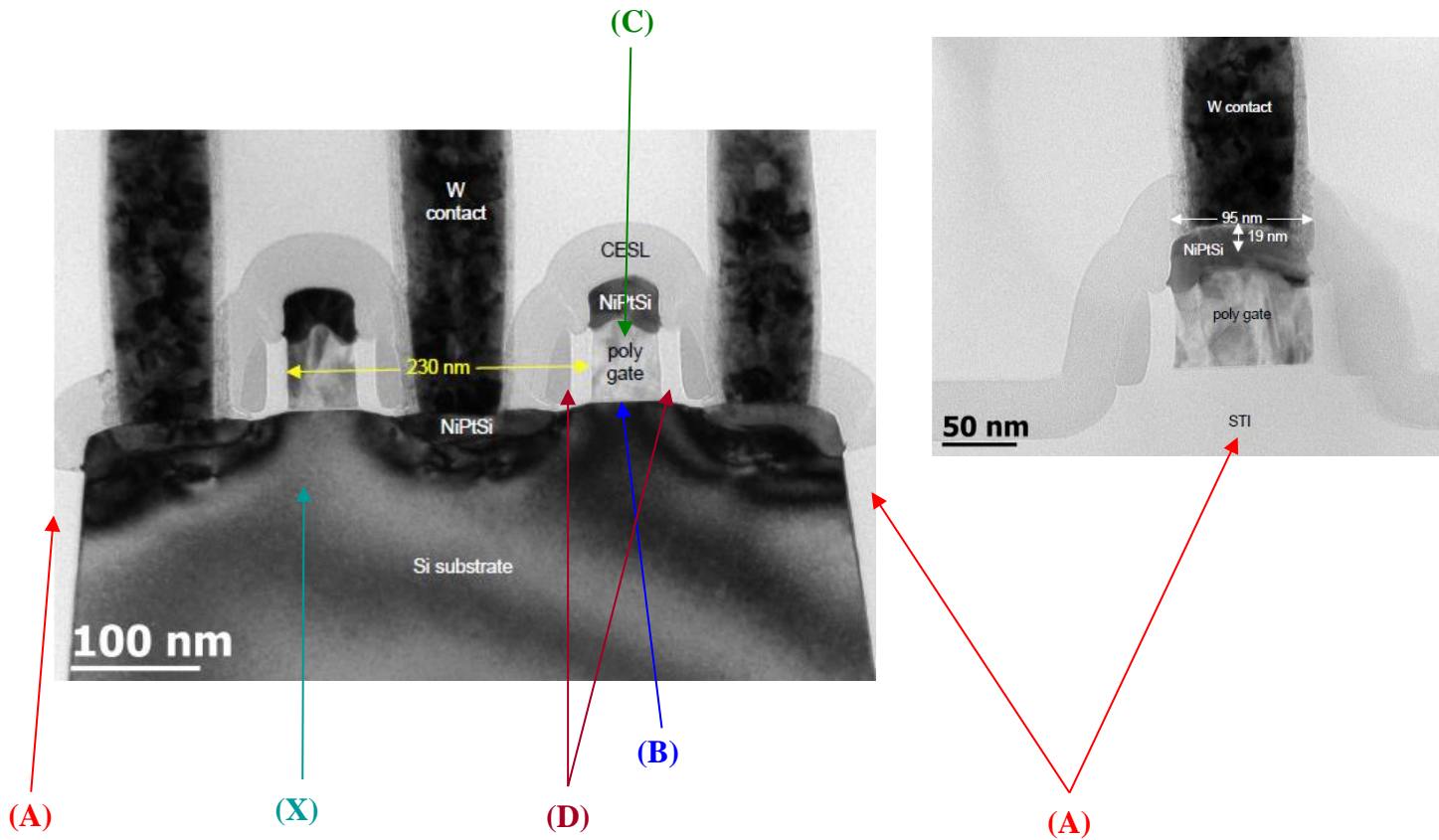
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1. A semiconductor device, comprising:

- (A) a trench isolation surrounding (X) an active area of a semiconductor substrate;
- (B) a gate insulating film formed over the active area;
- (C) a gate electrode formed over the gate insulating film;
- (D) first L-shaped sidewalls formed over the side surfaces of the gate electrode;
- (E) first silicide layers formed on regions located on the sides of the first L-shaped sidewalls within the active area[;]
- (F) an interconnection formed on the trench isolation; and
- (G) second L-shaped sidewalls formed over the side surfaces of the interconnection.

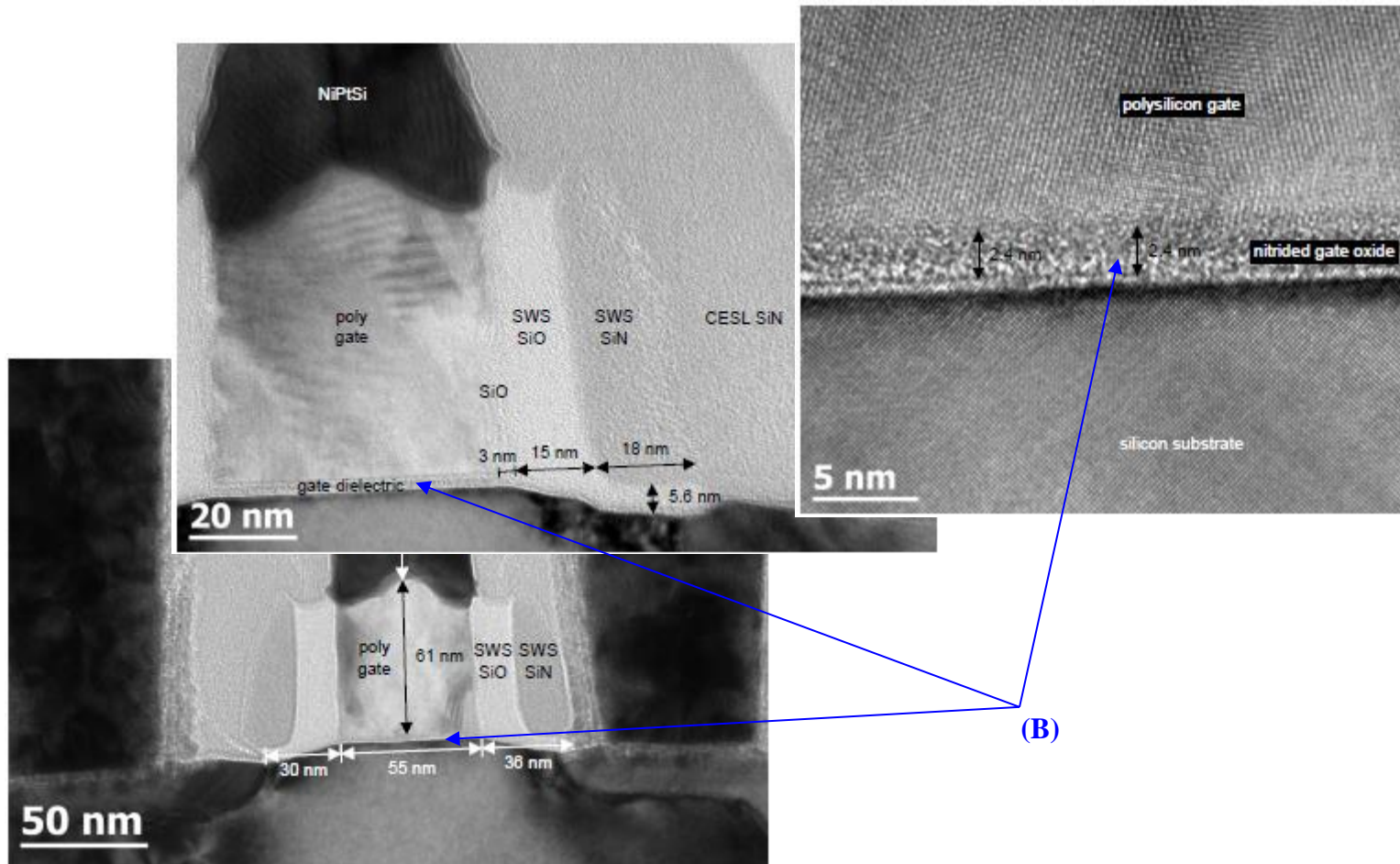
Claim 1

A semiconductor device, comprising: (A) a trench isolation surrounding (X) an active area of a semiconductor substrate; an insulating film formed over the active area; (C) a gate electrode formed over the gate insulating film; (D) first L-shaped conductive regions formed over the side surfaces of the gate electrode;



Claim 1

A semiconductor device, comprising: (A) a trench isolation surrounding (X) an active area of a semiconductor substrate; (B) an insulating film formed over the active area; (C) a gate electrode formed over the gate insulating film; (D) first L-shaped spacers formed over the side surfaces of the gate electrode;



Claim 1

(E) first silicide layers formed on regions located on the sides of the first L-shaped sidewalls within the active area [ ; ] (interconnection formed on the trench isolation; and (G) second L-shaped sidewalls formed over the side surfaces of the interconnection.

